Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.


# Electronic Supplementary Material

## Multilayer $MoS_2$ Growth by Metal and Metal-Oxide Sulfurization

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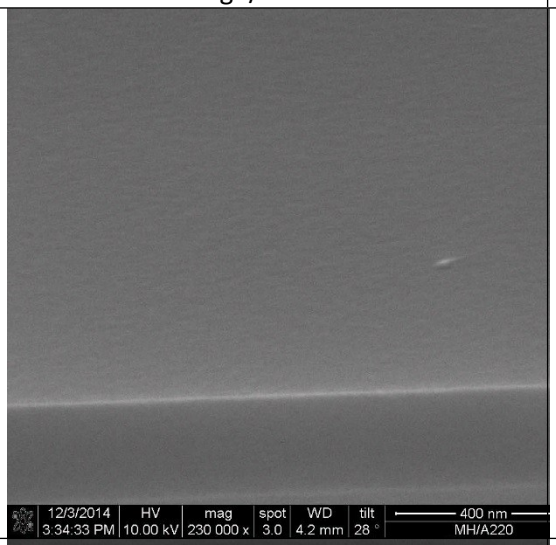
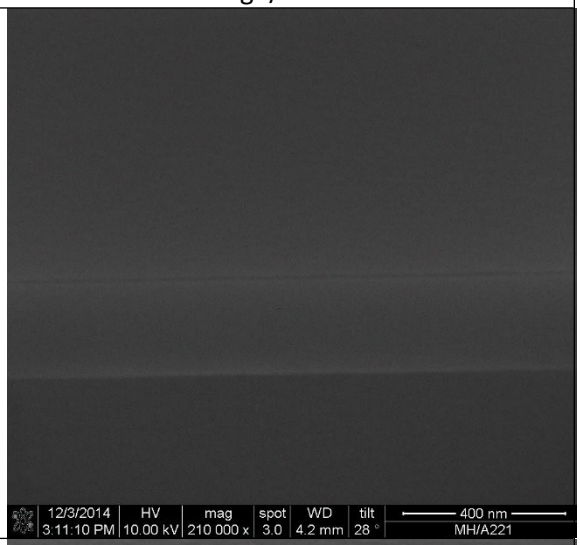
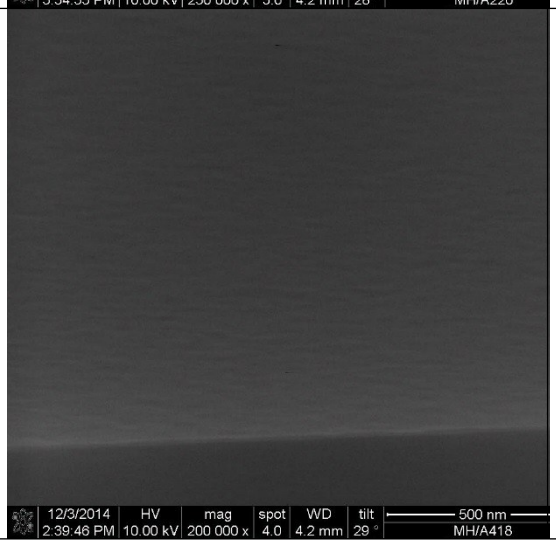
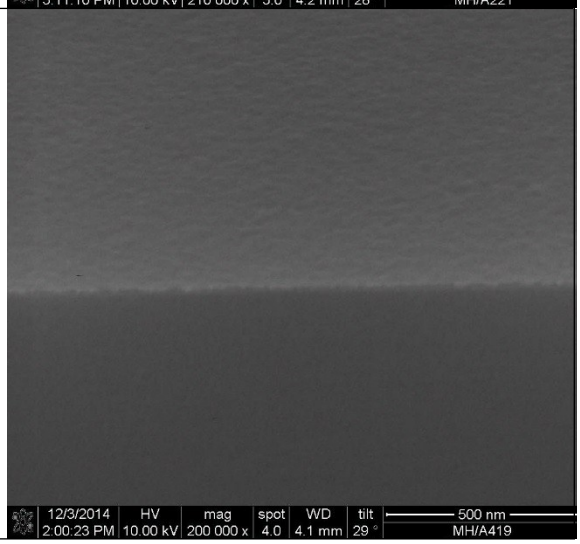
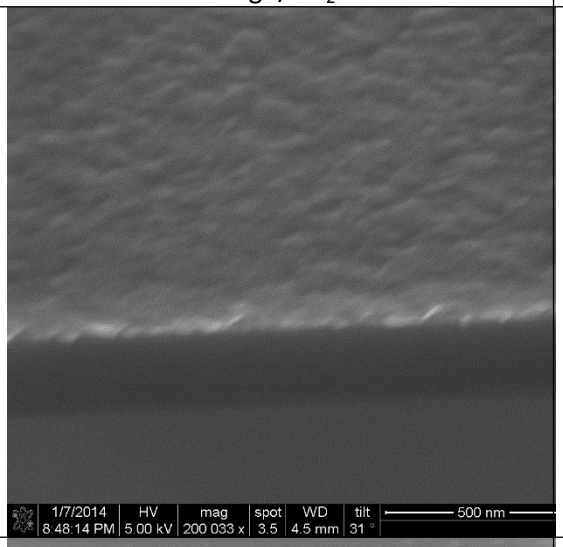
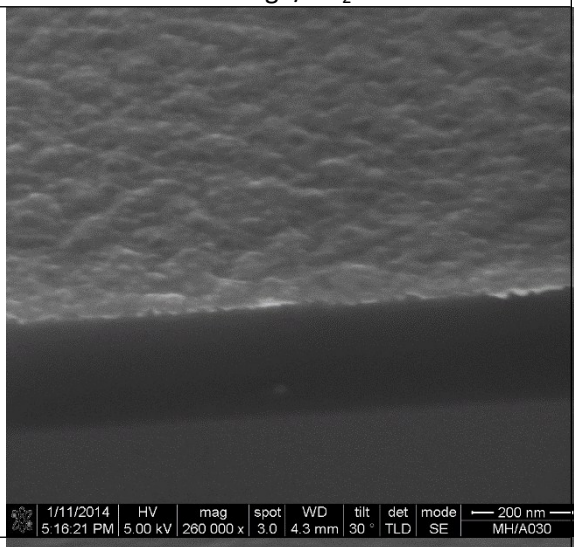
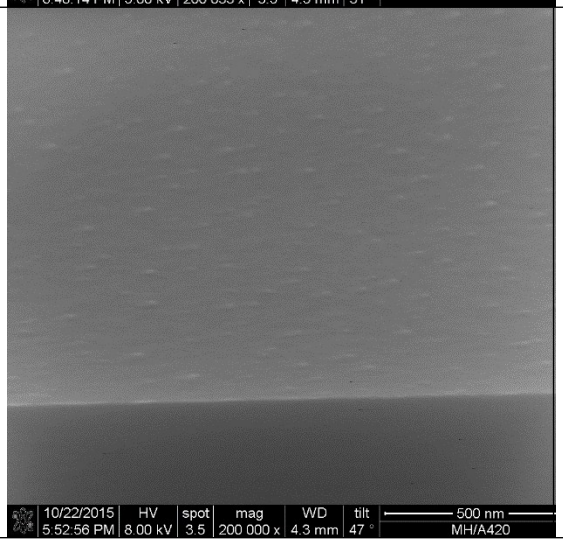
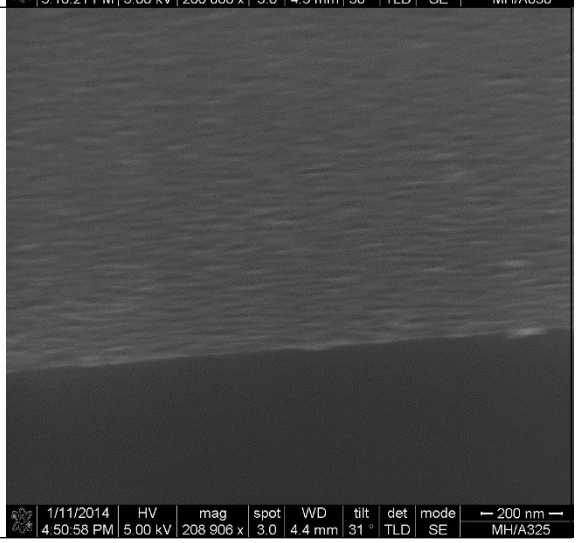
*S1: SEM images after vacuum annealing at different ramp rates.*

| Stack | 5 degC/s vacuum | 15 degC/s vacuum |
|---|---|---|
| B |   |   |
| C |   |   |

*S2: SEM images after $H_2S$ annealing at different ramp rates.*

| Stack | 5 degC/s $H_2S$ | 15 degC/s $H_2S$ |
|---|---|---|
| B |   |   |
| C |   |   |